(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
4 August 2011 (04.08.2011)

PCT

(10) International Publication Number
WO 2011/094038 A2

(51) International Patent Classification: Not classified

(21) International Application Number:
PCT/US2011/020283

(22) International Filing Date:
5 January 2011 (05.01.2011)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
12/694,134 26 January 2010 (26.01.2010) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declarations under Rule 4.17:

— *as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))*

Published:

— *without international search report and to be republished upon receipt of that report (Rule 48.2(g))*

(54) **Title**: METHOD AND APPARATUS FOR PATTERN COLLAPSE FREE WET PROCESSING OF SEMICONDUCTOR DEVICES

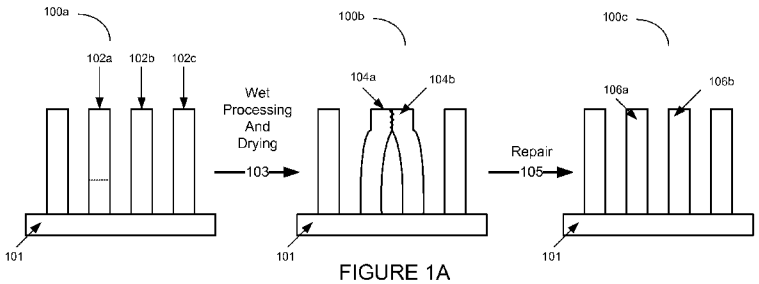


FIGURE 1A

(57) **Abstract**: A method is provided for processing a wafer used in fabricating semiconductor devices. The method can comprise forming high-aspect ratio features on the wafer, which is followed by wet processing and drying. During drying, pattern collapse can occur. This pattern collapse can be repaired to allow for additional processing of the wafer. In some instance, pattern collapse can be repaired via etching where the etching breaks bonds that can have formed during pattern collapse.

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